

# Smooth High at% Silicon SiCH and Ultra-thin SiCH Capsules

M.L. Hoppe Sr., C. Shulberg T. Reuter S. Earney, R. Luo, C. Bellew

General Atomics, San Diego, CA 92121  
IFTNP2024-015



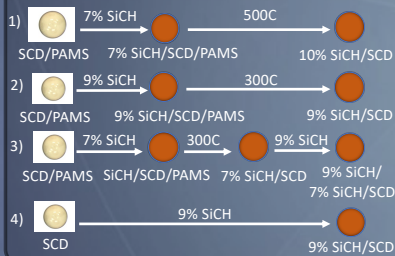
## Experimental Objective

SiCH Capsule Goal: Smooth, cryo-quality, multilayered capsule with at least 9at% Si outer layer and SCD (strong CD) inner layer.

Reason: Enable mapping of high silicon content CH layers (>7at% Si) to determine optimum Si content for maximum yield at shot time.

Side Goal: Determined thinnest free-standing capsule that can be produced.

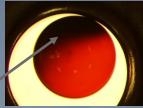
## Four Routes for High Si Content SiCH/SCD Capsule Explored



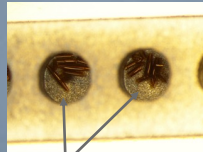
## Method 1 - Pyro of 7% SiCH/SCD at 500C under N<sub>2</sub>

SiCH layer (10+ at% Si) after pyrolysis SCD almost disappears.

Dark area is SCD residue

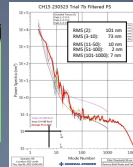
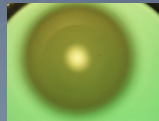


## Method 2 – 9+at% Si on thin SCD pre-PAMS removal not viable



Stress during PAMS pyro rips shell apart

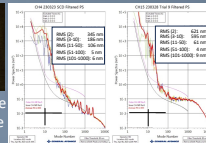
## Method 3 – 1.3μm 7% Si on 2.3μm SCD pre-PAMS; 1.6μm 9% Si deposited on SiCH/SCD post-PAMS



## Method 4 – Deposit 9% SiCH onto 2.6μm SCD capsule after PAMS pyro somewhat successful



SCD layer must be >2.6μm to reduce low mode roughness



High aspect ratio silicon doped GDP (6at% Si) have higher buckle pressure than un-doped GDP or SCD

Batch	OD (μm)	Wall (μm)	Survive 15 psia buckle	Survive 30 psia buckle	Youngs Modulus E (Gpa)
CH15-340526	~3100	6.5	No		<4.9
CH2-110815	~3150	8.8	Yes	No	>2.7 <5.4
CH2-100215	~3200	10.1	Yes	Yes	>4.0

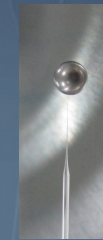
Normal GDP expected buckle pressure (max) for 3150x8.8 μm 10.5 PSI

SCD expected buckle pressure (max) for 3150x8.8 μm 15.5PSI

E (normal GDP) = 1.9 Gpa

E (SCD) = 2.4 Gpa

Superior buckle pressure allows for 3mm CFTA builds with capsules having <10μm wall thickness



3.1mmx6.5μm SiCH (5at% Si) pre 1 atm buckle test